

#### Features

- Four Channels of EMI Filtering with Integrated ESD Protection
- Pi–Style EMI Filters in a Capacitor–Resistor–Capacitor (C–R–C) Network
- ±15 kV ESD Protection on Each Channel (IEC 61000-4-2 Level 4, Contact Discharge)
- ±30 kV ESD Protection on Each Channel (HBM)
- Greater than -35 dB Attenuation (Typical) at 1 GHz

| Symbol             | Parameter  | Conditions   | Min         | Тур         | Max         | Units |
|--------------------|--|--|-------------|-------------|-------------|-------|
| R                  | Resistance   |  | 80          | 100         | 120         | Ω     |
| C <sub>TOTAL</sub> | Total Channel Capacitance  | At 2.5 VDC Reverse Bias,<br>1 MHz, 30 mVAC                         | 14          | 17          | 22          | pF    |
| С                  | Capacitance C  | At 2.5 VDC Reverse Bias,<br>1 MHz, 30 mVAC                         |             | 8.5         |             | pF    |
| V <sub>DIODE</sub> | Standoff Voltage   | I <sub>DIODE</sub> = 10 μA   |             | 6.0         |             | V     |
| I <sub>LEAK</sub>  | Diode Leakage Current (reverse bias)   | $V_{\text{DIODE}} = 3.3 \text{ V}$                                 |             | 0.1         | 1.0         | μΑ    |
| V <sub>SIG</sub>   | Signal Clamp Voltage<br>Positive Clamp<br>Negative Clamp   | $I_{LOAD} = 10 \text{ mA}$<br>$I_{LOAD} = -10 \text{ mA}$          | 5.6<br>-1.5 | 6.8<br>-0.8 | 9.0<br>-0.4 | V     |
| V <sub>ESD</sub>   | In–system ESD Withstand Voltage<br>a) Human Body Model, MIL–STD–883, Method 3015<br>b) Contact Discharge per IEC 61000–4–2 Level 4 | (Notes 2 and 3)  | 30<br>15    |             |             | kV    |
| R <sub>DYN</sub>   | Dynamic Resistance<br>Positive<br>Negative   |  |             | 2.3<br>0.9  |             | Ω     |
| f <sub>C</sub>     | Cut–off Frequency $Z_{SOURCE} = 50 \Omega$ , $Z_{LOAD} = 50 \Omega$  | Channel R = 100 $\Omega$ ,<br>Channel C <sub>SINGLE</sub> = 8.5 pF |             | 200         |             | MHz   |

### Table 4. ELECTRICAL OPERATING CHARACTERISTICS (Note 1)

T<sub>A</sub> = 25°C unless otherwise specified.
ESD applied to input and output pins with respect to GND, one at a time.
These parameters are guaranteed by design and characterization.

#### **PERFORMANCE INFORMATION**

Typical Filter Performance (T<sub>A</sub> = 25°C, DC Bias = 0 V, 50  $\Omega$  Environment)

1- -5. 28FF0 48

Figure 1. Insertion Loss vs. Frequency (FILTER1 Input to GND)

Figure 2. Insertion Loss vs. Frequency (FILTER2 Input to GND)

## PERFORMANCE INFORMATION (Cont'd)

Typical Filter Performance (T<sub>A</sub> = 25°C, DC Bias = 0 V, 50  $\Omega$  Environment)

Figure 3. Insertion Loss vs. Frequency (FILTER3 Input to GND)



Figure 4. Insertion Loss vs. Frequency (FILTER4 Input to GND)

CM1408



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